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Conference Proceedings Conference Proceedings	1 A self-aligned inverse-T gate fully overlapped LDD device for sub-half micron CMOS
Search - By Author - Basic - Advanced	Wen, D.S.; Hsu, C.CH.; Taur, Y.; Zicherman, D.S.; Wordeman, M.R.; Ning, T. Electron Devices Meeting, 1989. Technical Digest., International, 3-6 Dec. 198 Page(s): 765 -768
Member Services	[Abstract] [PDF Full-Text (216 KB)] IEEE CNF
O- Join IEEE O- Establish IEEE Web Account O- Access the IEEE Member Digital Library ☐ Print Format	2 Self-aligned silicided inverse-T gate LDD devices for sub-half micron technology Chen, ML.; Hillenius, S.J.; Juengling, W.; Yang, T.S.; Kornblit, A.; Lindenberge W.S.; Swiderski, J.A.; Favreau, D.P.; Electron Devices Meeting, 1990. Technical Digest., International, 9-12 Dec. 19 Page(s): 829 -832

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3 A self-aligned LDD/channel implanted ITLDD process with selectively deposited poly gates for CMOS VLSI

Pfiester, J.R.; Baker, F.K.; Sivan, R.D.; Crain, N.; Lin, H.-H.; Liaw, M.; Seelbach Gunderson, C.; Denning, D.;

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O- Advanced Member Services O- Join IEEE O- Establish IEEE Web Account O- Access the IEEE Member Digital Library ➡ Print Format	[Abstract] [PDF Full-Text (340 KB)] IEEE CNF 152 Development of GaAs pseudomorphic HEMTs at W-band Zhu Guoliang; Yuan Mingwen; Liu Chenhui; Qiu Wei; Nie Huijun; Millimeter Wave and Far Infrared Science and Technology, 1996. Proceedings. 4 International Conference on , 12-15 Aug. 1996 Page(s): 66 -69
	[Abstract] [PDF Full-Text (172 KB)] IEEE CNF 153 Fault-tolerant quantum computation Shor, P.W.; Foundations of Computer Science, 1996. Proceedings., 37th Annual Symposium 14-16 Oct. 1996 Page(s): 56 -65 [Abstract] [PDF Full-Text (912 KB)] IEEE CNF

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